TLX9185A

TOSHIBA Photocoupler IRLED & Photo-Transistor

TLX9185A

 \bigcirc Various Controllers

TOSHIBA

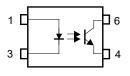
- Signal transmission between different circuit potential
- HEV (Hybrid Electric Vehicle) and EV (Electric Vehicle) Applications

The TOSHIBA TLX9185A mini-flat photocoupler is suitable for surfacemount assembly. The TLX9185A consists of an infrared LED optically coupled to a photo-transistor.

This photocoupler can be used to the extensive applications. It is generic speed transistor output.

- Collector-emitter voltage: 80 V (min)
- Current transfer ratio: 50% (min) to 600%(max) Rank GB: 100% (min) to 600%(max)
- Isolation voltage: 3750 Vrms (min)
- AEC-Q101 qualified

Pin Configuration



1: Anode 3: Cathode 4: Emitter 6: Collector Unit: mm

Weight: 0.08 g (typ.)

onate maximum ratings (rote) (oness otherwise specifica, ra = 20 o)							
Characteristic	Symbol	Rating	Unit				
Forward current	lF	30	mA				
Forward current (Ta=125°C)	lF	18	mA				
Econvard current derating (Ta > $108 ^{\circ}\text{C}$)		-0.7	mA/°C				

Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25°C)

		-		
Forward current derating (Ta ≥ 108 °C)		ΔI _F /°C	-0.7	mA/°C
Pulse forward current	(Note 1)	IFP	1	А
Input Power Dissipation		PD	50	mW
Input Power Dissipation Derating (Ta \geq 50°C)		ΔPD/°C	-0.5	mW/°C
Reverse voltage		VR	5	V
Collector-emitter voltage		V _{CEO}	80	V
Emitter-collector voltage		V _{ECO}	7	V
Collector current		Ic	50	mA
Collector power dissipation		Pc	150	mW
Collector power dissipation derating (Ta \ge 50°C)		ΔP _C /°C	-1.5	mW/°C
erating temperature range		T _{opr}	-40 to 125	°C
rage temperature range		T _{stg}	-55 to 150	°C
Lead soldering temperature (10 s)		T _{sol}	260	°C
Total package power dissipation		PT	200	mW
al package power dissipation derating (Ta \ge 50°C)		ΔP _T /°C	-2.0	mW/°C
ation voltage (AC, 60 s, R.H. ≤ 60 %)	(Note 2)	BVS	3750	Vrms
	Pulse forward current Input Power Dissipation Input Power Dissipation Derating (Ta \geq 50°C) Reverse voltage Collector-emitter voltage Emitter-collector voltage Collector current Collector power dissipation Collector power dissipation derating (Ta \geq 50°C) erating temperature range rage temperature range d soldering temperature (10 s)	Pulse forward current(Note 1)Input Power DissipationInput Power Dissipation Derating (Ta $\geq 50^{\circ}$ C)Reverse voltageCollector-emitter voltageCollector-emitter voltageCollector currentCollector power dissipationCollector power dissipation derating (Ta $\geq 50^{\circ}$ C)Collector power dissipation derating (Ta $\geq 50^{\circ}$ C)Collector power dissipation derating (Ta $\geq 50^{\circ}$ C)Emitter-collector voltageCollector power dissipation derating (Ta $\geq 50^{\circ}$ C)Collector power dissipation derating temperature rangeCollector power dissipation derating (Ta $\geq 50^{\circ}$ C)End package power dissipation derating (Ta $\geq 50^{\circ}$ C)Collector power dissipation	Pulse forward current(Note 1)IFPInput Power DissipationPDInput Power Dissipation Derating (Ta ≥ 50°C) Δ PD/°CReverse voltageVRCollector-emitter voltageVCEOEmitter-collector voltageVECOCollector currentICCollector power dissipation derating (Ta ≥ 50°C) Δ PC/°Cerating temperature rangeToprrage temperature rangeTstgd soldering temperature (10 s)Tsolal package power dissipation derating (Ta ≥ 50°C) Δ PT/°C	Pulse forward current(Note 1)IFP1Input Power DissipationPD50Input Power Dissipation Derating (Ta ≥ 50°C)ΔPD/°C-0.5Reverse voltageVR5Collector-emitter voltageVCEO80Emitter-collector voltageVECO7Collector currentIC50Collector power dissipation derating (Ta ≥ 50°C)ΔPC/°C-1.5Collector power dissipation derating (Ta ≥ 50°C)ΔPC/°C-1.5collector power dissipation derating (Ta ≥ 50°C)Topr-40 to 125rage temperature rangeTstg-55 to 150d soldering temperature (10 s)Tsol260al package power dissipation derating (Ta ≥ 50°C)ΔPT/°C-2.0

Note : Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width PW \leq 100 μ s, f = 100 Hz

Note 2: This device is considered as a two terminal device: Pins 1 and 3 are shorted together, and pins 4 and 6 are shorted together.

Recommended Operating Conditions (Note)

Characteristic	Symbol	Min	Тур.	Max	Unit
Supply voltage	Vcc	_	5	48	V
Forward current	lF	_	10	15	mA
Collector current	IC		1	10	mA
Operating temperature (Note 1)	Topr	-40	_	125	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Note 1: Denotes the operating range, not the recommended operating condition.

Electrical Characteristics (Unless otherwise specified, Ta = -40 to 125°C)

	Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
	Converd veltage	\/-	I _F = 10 mA, Ta = 25 °C	1.1	1.27	1.4	V
Ģ	Forward voltage	VF	IF = 10 mA	1.0	_	1.55	V
LED	Reverse current	IR	V _R = 5 V	_	_	10	μA
	Capacitance	Ст	V = 0 V, f = 1 MHz, Ta = 25 °C	_	35	_	pF
	Collector-emitter breakdown voltage	V(BR) CEO	IC = 0.5 mA	80	_	_	V
or	Emitter-collector breakdown voltage	V(BR) ECO	IE = 0.1 mA	7	_	_	V
Detector			V _{CE} = 48 V, Ta = 25 °C	_	10	100	nA
ð	Collector dark current	ICEO	V _{CE} = 48 V, Ta = 105 °C	_	5	50	μA
			V _{CE} = 48 V, Ta = 125 °C	_	30	100	μA
	Capacitance (collector to emitter)	CCE	V = 0 V, f = 1 MHz, Ta = 25 °C	_	10	—	pF

Coupled Electrical Characteristics (Unless otherwise specified, Ta = -40 to 125°C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
		I _F = 5 mA, V _{CE} = 5 V	20	_	600	%
Current transfer ratio	I _C / I _F	I _F = 5 mA, V _{CE} = 5 V, Ta = 25 °C	50	_	600	70
		IF = 5 mA, V _{CE} = 5 V , Ta = 25 °C Rank GB	100	_	600	%
Saturated CTR IC / IF (sat)		IF = 1 mA, V _{CE} = 0.4 V, Ta = 25 °C	_	200		
	I _F = 1 mA, V _{CE} = 0.4 V, Ta = 25 °C Rank GB	30	_	_	%	
		IC = 2.4 mA, IF = 8 mA, Ta = 25 °C	—	_	0.4	
Collector-emitter VCE (sat)	V _{CE (sat)}	IC = 0.2 mA, IF = 1 mA	—	—	0.4	V
		Ta=25 °C	_	0.1	0.4	
Off-state collector current	I _{C (off)}	V_{F} = 0.7V, V_{CE} = 48 V , Ta = 25 °C	_	_	10	μA

Isolation Characteristics (Ta = 25°C)

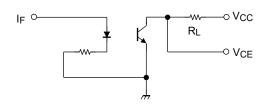
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance (input to output)	Cs	V _S = 0 V, f = 1 MHz	_	0.5	_	pF
Isolation resistance	Rs	Vs = 500 V, R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴	_	Ω
Isolation voltage	BVs	AC, 60 s	3750	_	_	Vrms

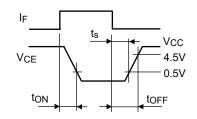
Note : This device is considered as a two terminal device: Pins 1 and 3 are shorted together, and pins 4 and 6 are shorted together.

Switching Characteristics (Ta = 25°C)

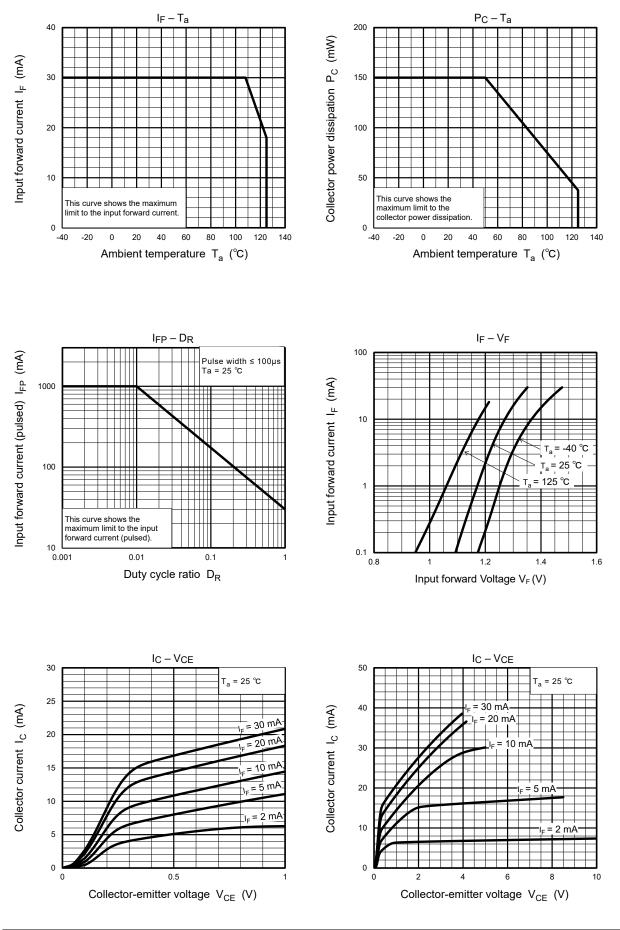
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Rise time	tr		—	3	—	
Fall time	tf	V _{CC} = 10 V, I _C = 2 mA R _L = 100 Ω	_	5	_	
Turn-on time	ton		_	5	_	μs
Turn-off time	toff		_	5	_	
Turn-on time	ton			2		
Storage time	ts	$R_L = 1.9 k\Omega$ (Note 1 V _{CC} = 5 V, I _F = 16 mA	_	25	_	μS
Turn-off time	toff		_	45	_	

Note 1: Switching time test circuit

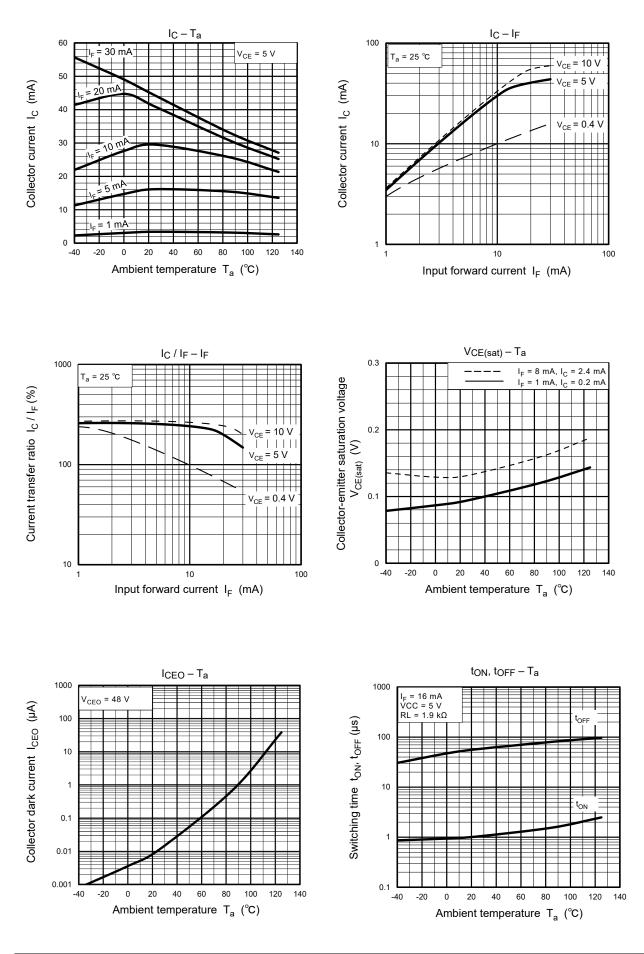


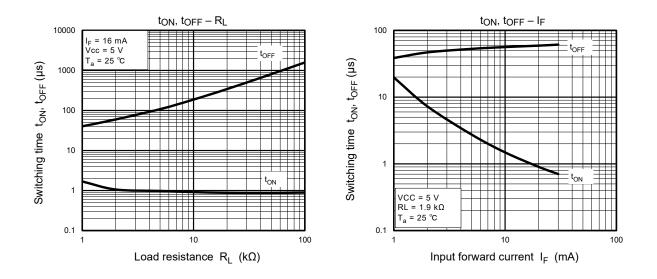


Characteristic Curves (Note)



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Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise specified

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